

<IGBT Modules>

CM800DW-24T

HIGH POWER SWITCHING USE
INSULATED TYPE



Collector current I_c **800 A**
 Collector-emitter voltage V_{CES} **1200 V**
 Maximum junction temperature T_{vjmax} **175 °C**

- Dual switch (Half-bridge)
- Copper base plate (Nickel-plating)
- Ni-plating signal terminals
- RoHS Directive compliant
- UL Recognized under UL1557, File No. E323585

APPLICATION

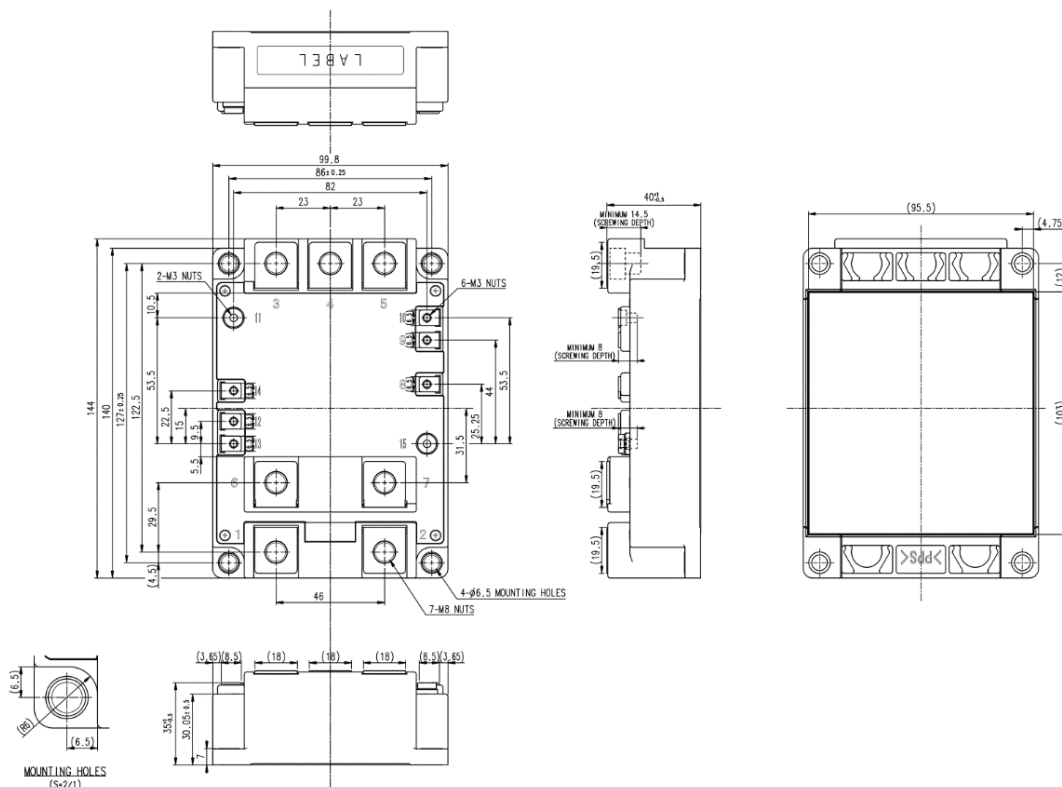
AC motor control, Photovoltaic (PV) inverter, Power supply etc,

OPTION (Below options are available.)

- PC-TIM (Phase Change Thermal Interface Material) pre-apply
- V_{CESat} selection for parallel connection

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



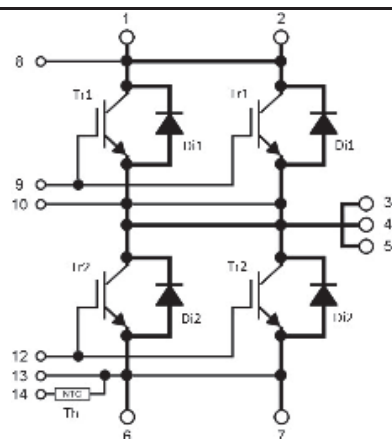
Tolerance otherwise specified		
Division of Dimension		Tolerance
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

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HIGH POWER SWITCHING USE

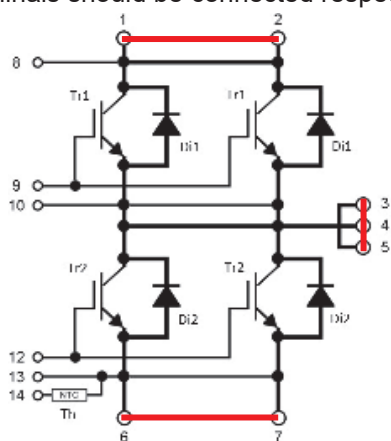
INSULATED TYPE

INTERNAL CONNECTION**TERMINAL CODE**

1. C1	9. G1
2. C1	10. Es1
3. C2E1	11. NC
4. C2E1	12. G2
5. C2E1	13. Es2, TH2
6. E2	14. TH1
7. E2	15. NC
8. Cs	

NOTE

Terminal 1 and 2, Terminal 3,4 and 5, Terminal 6 and 7,
These terminals should be connected respectively when it is used.



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MAXIMUM RATINGS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=(102)\text{ }^{\circ}\text{C}$ (Note.2, 4)	800	A
I_{CRM}		Pulse, Repetitive (Note.3)	1600	
P_{tot}	Total power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note.2,4)	3485	W
I_E (Note.4)	Emitter current	DC (Note.2)	800	A
I_{ERM} (Note.4)		Pulse, Repetitive (Note.3)	1600	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, $f=60\text{ Hz}$, AC 1 min	4000	V
T_{vjmax}	Maximum junction temperature	Instantaneous event (overload) (Note.9)	175	$^{\circ}\text{C}$
T_{Cmax}	Maximum case temperature	(Note.4,9)	125	$^{\circ}\text{C}$
T_{vjop}	Operating junction temperature	Continuous operation (Note.9)	-40 ~ +150	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ($T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited		-	-	1.0	mA
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited		-	-	0.5	μA
V _{GE(th)}	Gate-emitter threshold voltage	I _C =80 mA, V _{CE} =10 V		5.4	6	6.6	V
V _{CESat}	Collector-emitter saturation voltage	I _C =800 A ^(Note.5) , V _{GE} =15 V, (Terminal)	T _{vj} = 25 °C	-	1.55	1.90	V
			T _{vj} =125 °C	-	1.75	-	
			T _{vj} =150 °C	-	1.80	-	
		I _C =800 A ^(Note.5) , V _{GE} =15 V, (Chip)	T _{vj} = 25 °C	-	1.50	1.75	V
			T _{vj} =125 °C	-	1.70	-	
			T _{vj} =150 °C	-	1.75	-	
C _{ies}	Input capacitance	V _{CE} =10 V, V _{GE} =0V		-	-	194	nF
C _{oes}	Output capacitance			-	-	5.5	
C _{res}	Reverse transfer capacitance			-	-	2.4	
Q _G	Gate charge	V _{CC} =600 V, I _C =800 A, V _{GE} =15 V		-	6.0	-	μC
t _{d(on)}	Turn-on delay time	V _{CC} =600 V, I _E =800 A, V _{GE} =±15 V, R _G =1.6 Ω, Inductive load		-	-	800	ns
t _r	Rise time			-	-	200	
t _{d(off)}	Turn-off delay time			-	-	1200	
t _f	Fall time			-	-	400	
V _{EC} ^(Note.4)	Emitter-collector voltage	I _E =800 A ^(Note.5) , G-E short-circuited, (Terminal)	T _{vj} = 25 °C	-	1.65	2.00	V
			T _{vj} =125 °C	-	1.65	-	
			T _{vj} =150 °C	-	1.65	-	
		I _E =800 A ^(Note.5) , G-E short-circuited, (Chip)	T _{vj} = 25 °C	-	1.60	1.95	V
			T _{vj} =125 °C	-	1.60	-	
			T _{vj} =150 °C	-	1.60	-	
t _{rr} ^(Note.4)	Reverse recovery time	V _{CC} =600 V, I _E =800 A, V _{GE} =±15 V, R _G =1.6 Ω, Inductive load		-	-	400	ns
Q _{rr} ^(Note.4)	Reverse recovery charge			-	62.4	-	μC
E _{on}	Turn-on switching energy per pulse	V _{CC} =600V, I _C =I _E =800A, V _{GE} =±15V, R _G =1.6Ω, T _{vj} =150°C, Inductive load		-	72	-	mJ
E _{off}	Turn-off switching energy per pulse			-	94	-	
E _{rr} ^(Note.4)	Reverse recovery energy per pulse			-	57	-	
R _{CC'+EE'}	Internal lead resistance	Main terminals-chip T _C =25 °C ^(Note.4)		-	0.25	-	mΩ
r _g	Internal gate resistance	Per switch		-	0.50	-	Ω

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HIGH POWER SWITCHING USE
INSULATED TYPE

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	4.85	5.00	5.15	k Ω
$\Delta R/R$	Deviation of resistance	$R_{100}=493\text{ }\Omega$, $T_C=100\text{ }^{\circ}\text{C}$ (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per IGBT switch (Note.4)	-	-	43	K/kW
$R_{th(j-c)D}$		Junction to case, per FWDi switch (Note.4)	-	-	68	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module, Thermal grease applied (Note 4,7,9)	-	10	-	K/kW

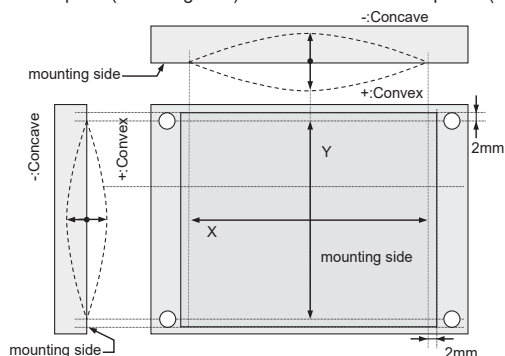
MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 8 screw	7.0	10.5	14.0	N·m
M_s		Mounting to heat sink M 6 screw	3.5	4.0	4.5	
M_t		Auxiliary terminals M 3 screw	0.4	0.5	0.6	
d_s	Creepage distance	Terminal to terminal	17	-	-	mm
		Terminal to base plate	30	-	-	mm
d_a	Clearance	Terminal to terminal	8.5	-	-	mm
		Terminal to base plate	28	-	-	mm
e_c	Flatness of base plate	On the centerline of X, Y (Note.8)	0	-	+200	μm
m	Mass	-	-	860	-	g

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU)2015/863.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_{vj}) should not increase beyond $T_{vj\max}$ rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed $T_{vj\max}$ rating.
- Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.
Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- $B(25/50) = \ln \left(\frac{R_{25}}{R_{50}} \right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}} \right)$
 R_{25} : resistance at absolute temperature T_{25} [K]; $T_{25}=25\text{ }^{\circ}\text{C}+273.15=298.15$ [K]
 R_{50} : resistance at absolute temperature T_{50} [K]; $T_{50}=50\text{ }^{\circ}\text{C}+273.15=323.15$ [K]
- Reference value. Thermally conductive grease of thermal conductivity $\lambda=0.9\text{ W/(m}\cdot\text{K)}$ and thickness $D(C-S)=50\text{ }\mu\text{m}$.
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



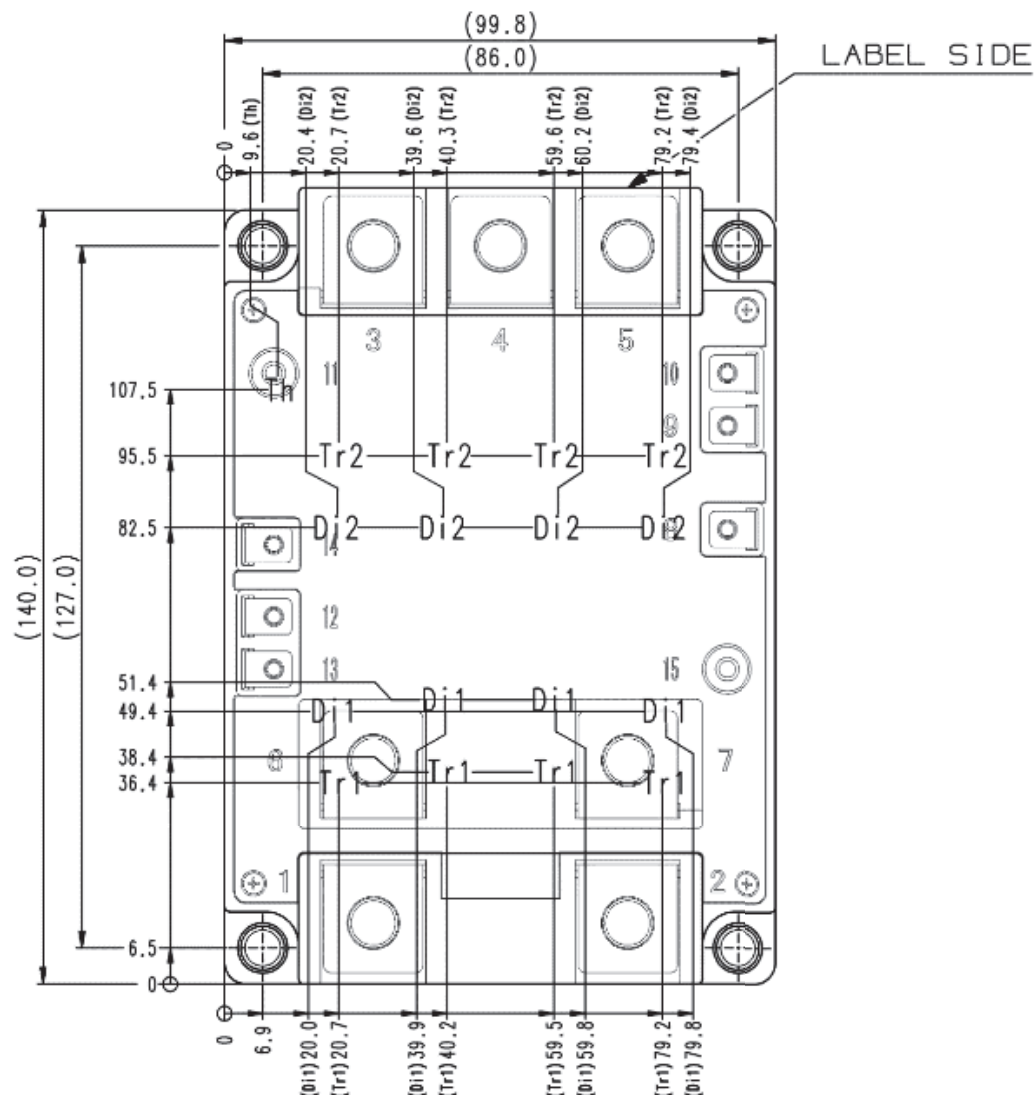
- Long term performance related to thermal conductive grease (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under user's specific application conditions. Each temperature condition ($T_{vj\max}$, $T_{vj\text{op}}$, $T_{C\max}$) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.

RECOMMENDED OPERATING CONDITIONS

CM800DW-24THIGH POWER SWITCHING USE
INSULATED TYPE

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	DC supply voltage	Applied across C1-E2 terminals	-	600	850	V
V_{GEon}	Gate-emitter drive voltage	Applied across G1-Es1/ G2-Es2 terminals	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	1.6	-	10	Ω

Optimum operating conditions should be selected with careful confirmation for no occurrence of any maximum rating violation (T_{vj} , V_{CES} , etc.) or any unexpected malfunction (arm-short-through, oscillation, etc.) at the actual application conditions.

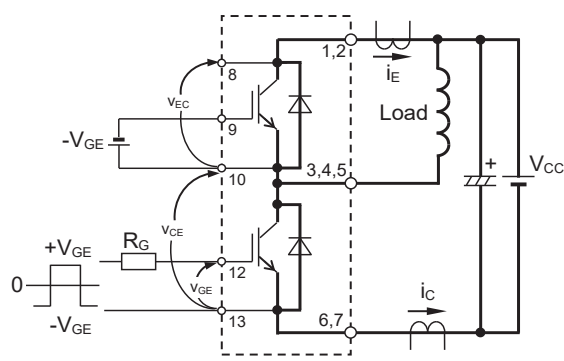
CHIP LOCATION (Top view)Dimension in mm, tolerance: ± 1 mm

Tr1/Tr2: IGBT, Di1/Di2: FWD, Th: NTC thermistor

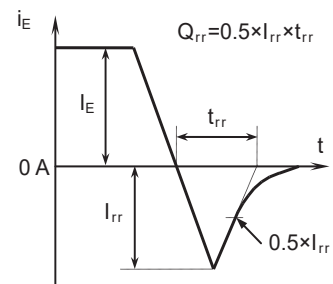
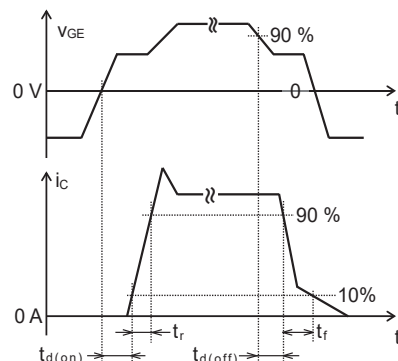
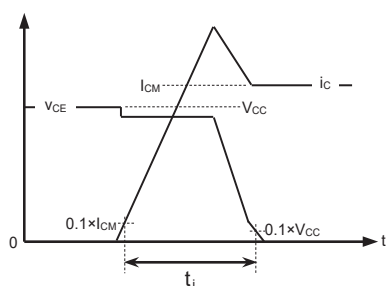
CM800DW-24T

HIGH POWER SWITCHING USE

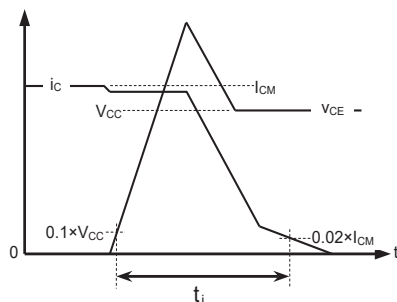
INSULATED TYPE

TEST CIRCUIT AND WAVEFORMS

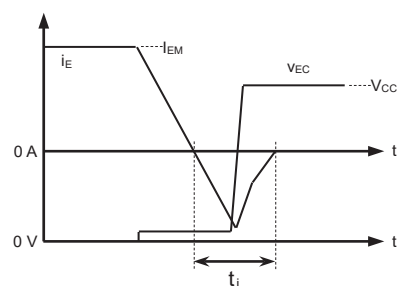
Switching characteristics test circuit and waveforms

 t_{rr} , Q_{rr} characteristics test waveform

IGBT Turn-on switching energy

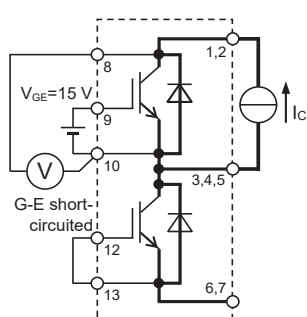


IGBT Turn-off switching energy

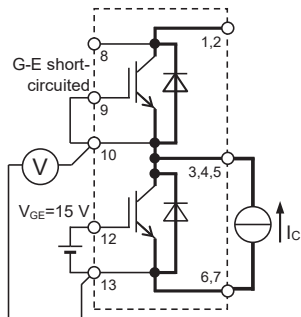


FWD Reverse recovery energy

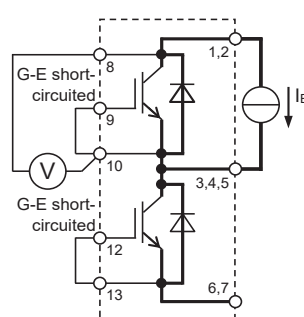
Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT

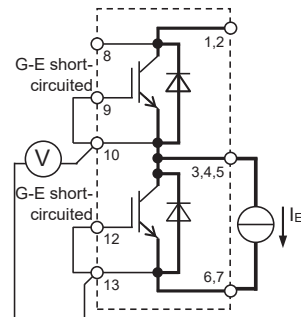
Tr1

 V_{CEsat} characteristics test circuit

Tr2



Di1

 V_{EC} characteristics test circuit

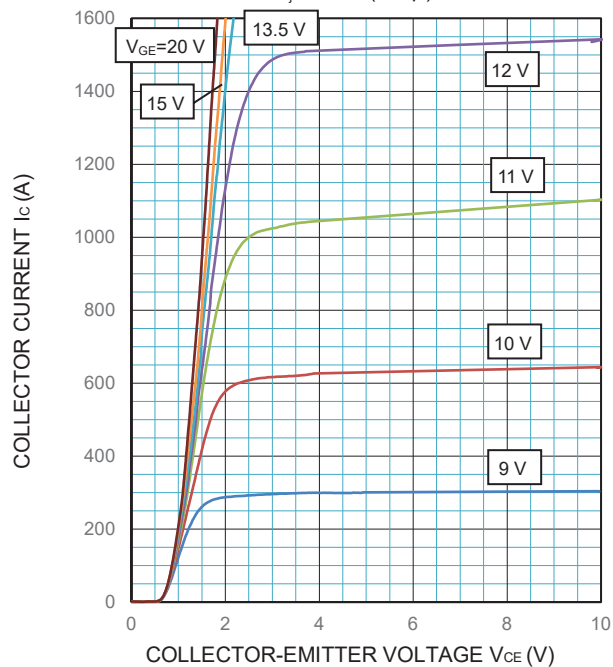
Di2

PERFORMANCE CURVES

INVERTER PART

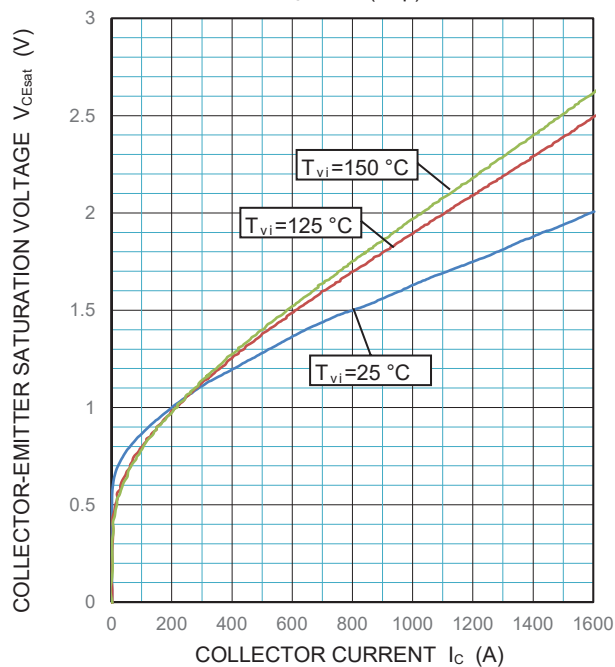
OUTPUT CHARACTERISTICS

(TYPICAL)

 $T_{vj}=25^{\circ}\text{C}$ (chip)

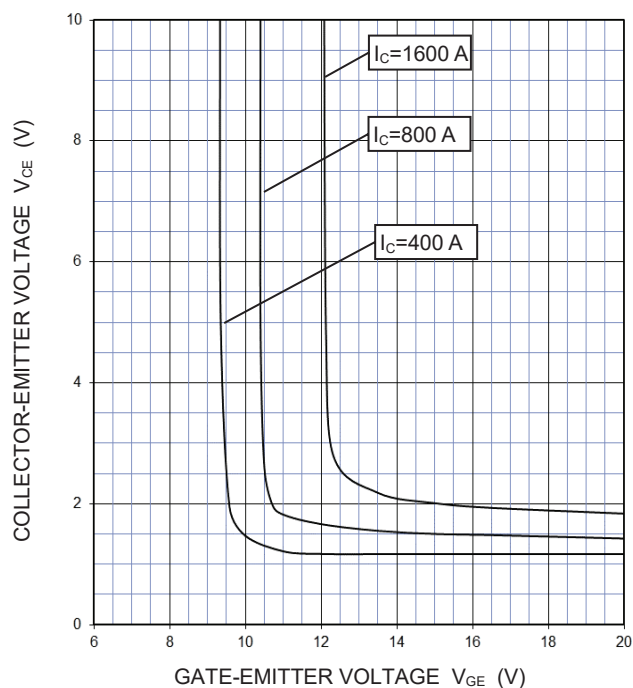
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS

(TYPICAL)

 $V_{ge}=15\text{V}$ (chip)

COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS

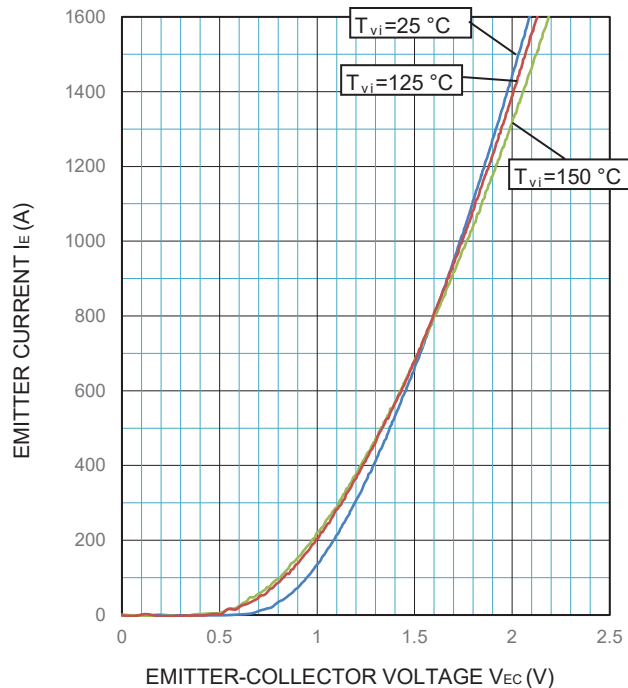
(TYPICAL)

 $T_{vj}=25^{\circ}\text{C}$ (chip)

FREE WHEELING DIODE FORWARD CHARACTERISTICS

(TYPICAL)

G-E short-circuited (chip)

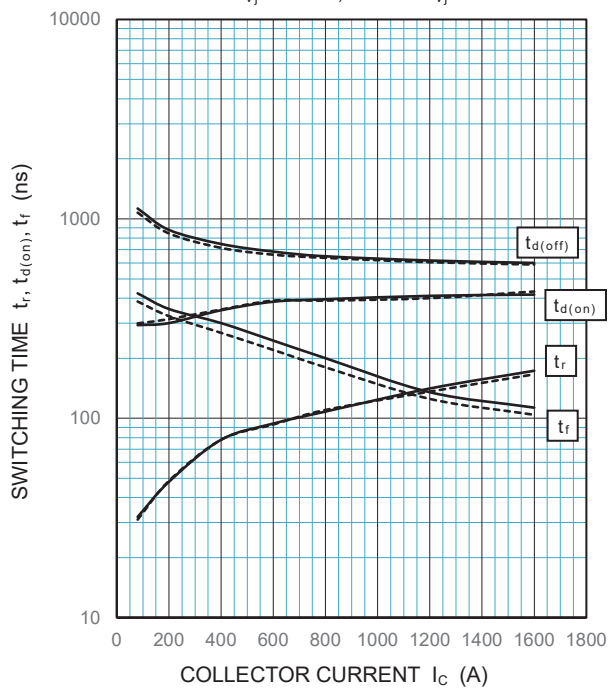


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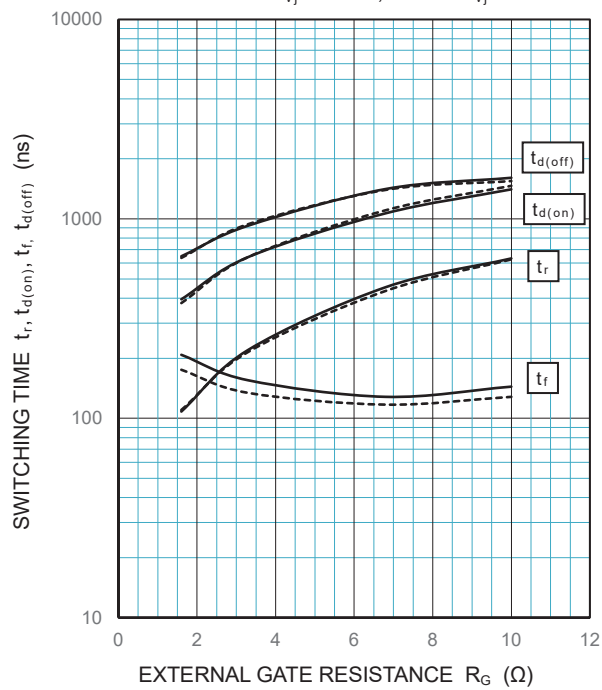
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES**INVERTER PART****HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)**

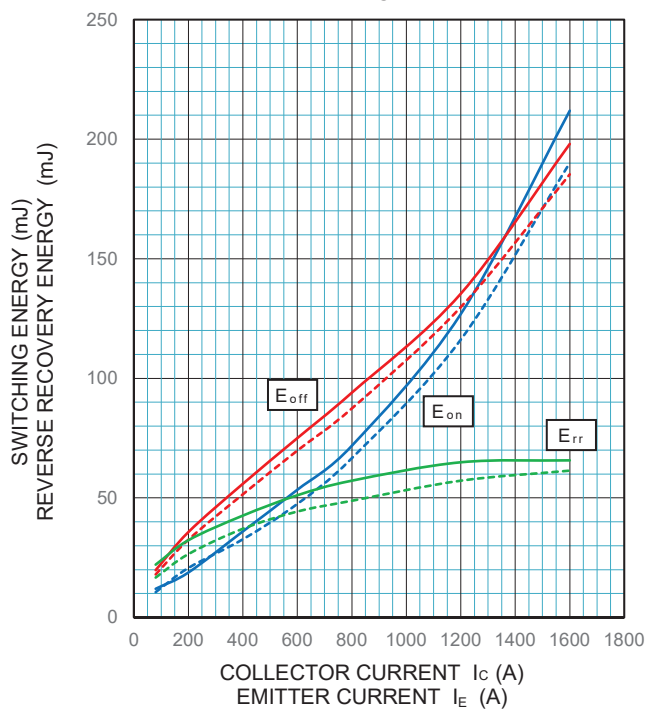
$V_{CC}=600\text{ V}$, $R_G=1.6\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$

**HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)**

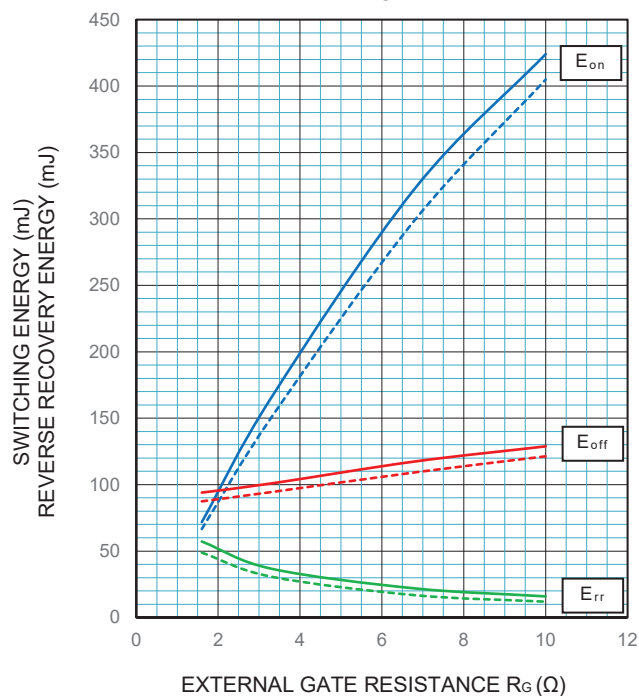
$V_{CC}=600\text{ V}$, $I_C=800\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$

**HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)**

$V_{CC}=600\text{ V}$, $R_G=1.6\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - -: $T_{vj}=125\text{ }^\circ\text{C}$,
PER PULSE

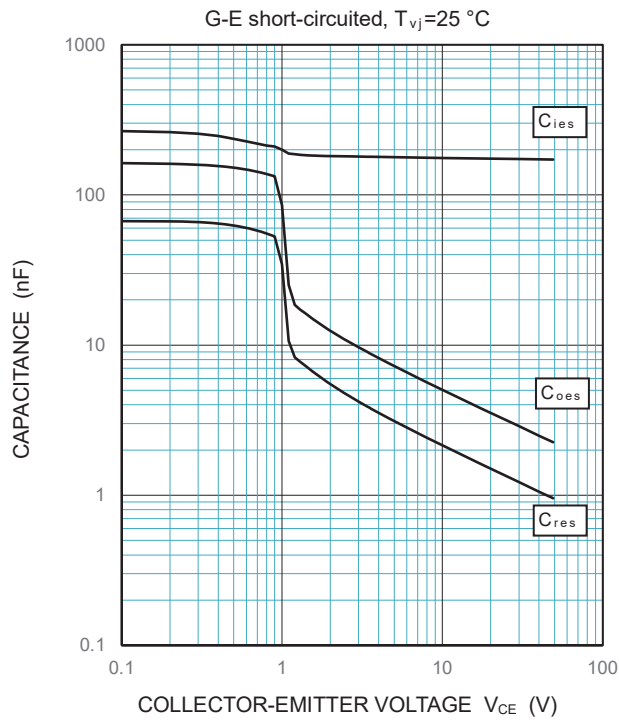
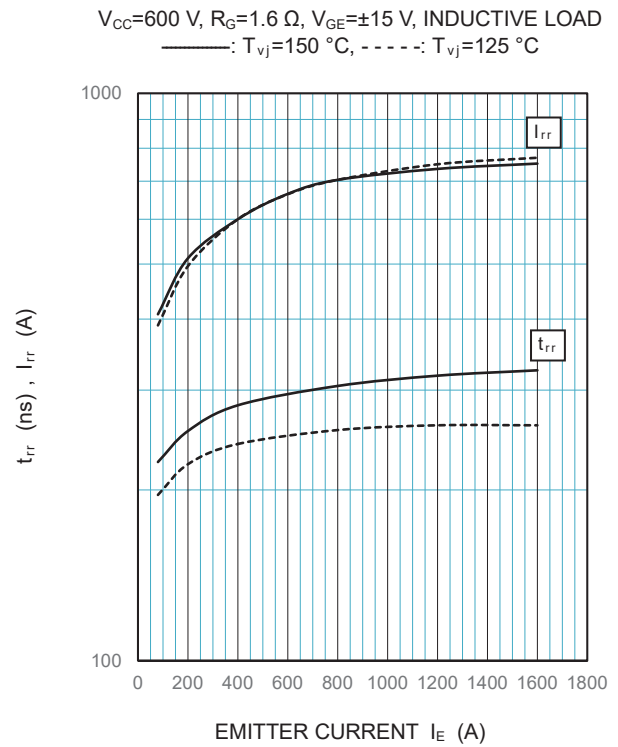
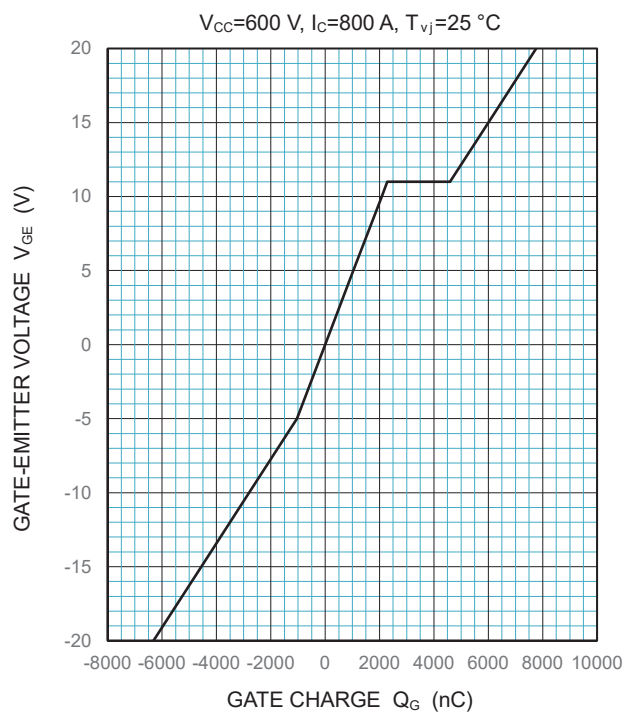
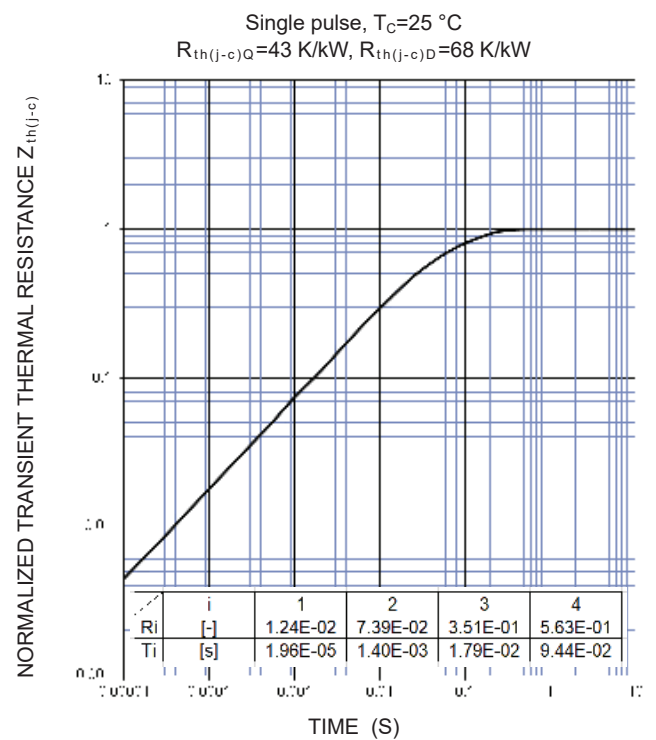
**HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)**

$V_{CC}=600\text{ V}$, $I_C/I_E=800\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - -: $T_{vj}=125\text{ }^\circ\text{C}$,
PER PULSE



PERFORMANCE CURVES

INVERTER PART

CAPACITANCE CHARACTERISTICS
(TYPICAL)FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)GATE CHARGE CHARACTERISTICS
(TYPICAL)TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)

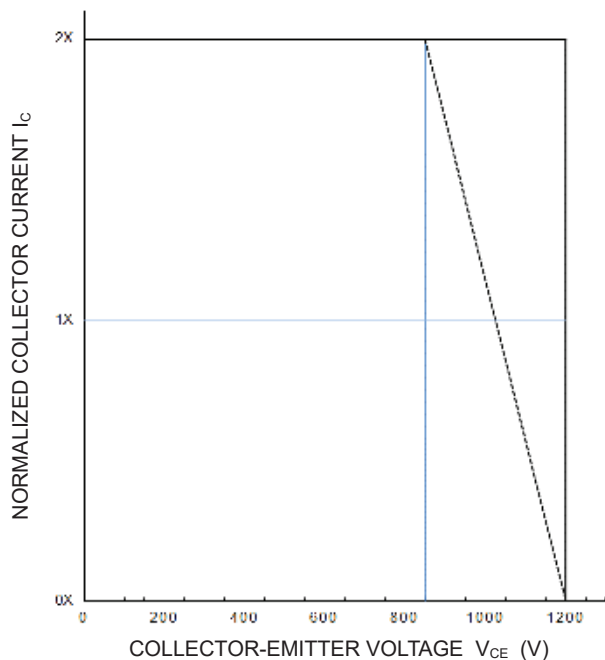
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HIGH POWER SWITCHING USE

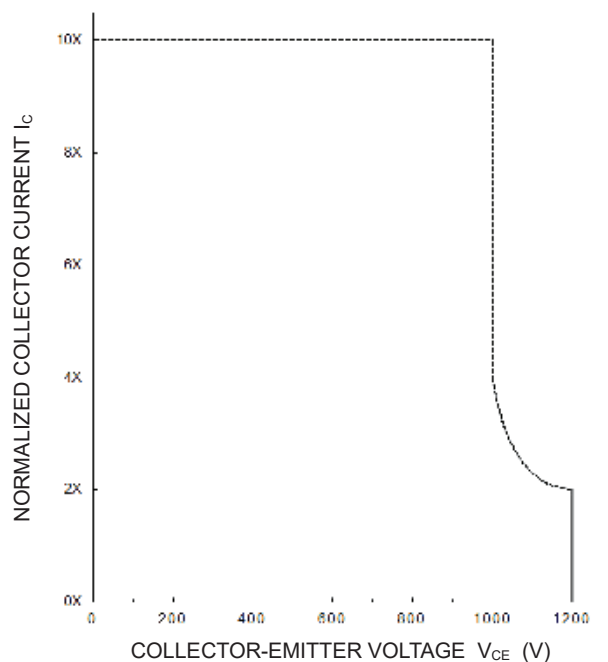
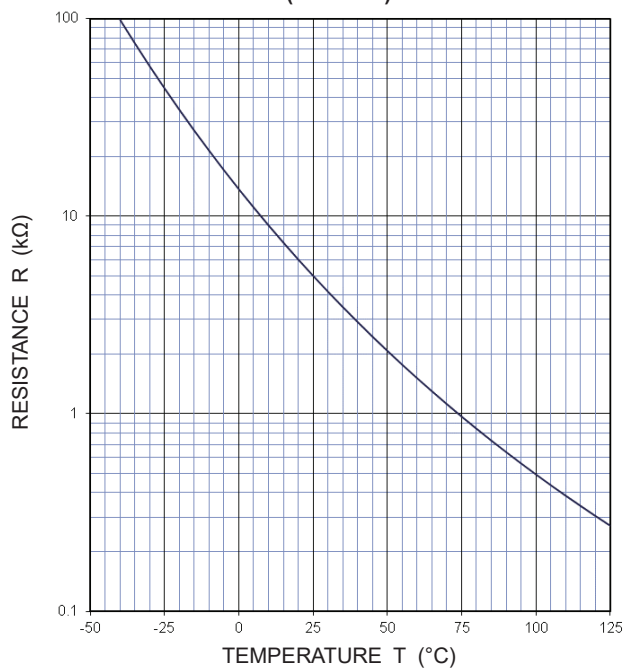
INSULATED TYPE

PERFORMANCE CURVES**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 850 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $R_{G(off)} = 1.6 \sim 10 \Omega$,
 —: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
 - - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))

**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 800 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \mu\text{s}$, Non-Repetitive

**NTC thermistor part****TEMPERATURE CHARACTERISTICS
(TYPICAL)**

Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Important Notice

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